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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	37
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10rjaafa-50

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1.3.4 52-pin products

• 52-pin plastic LQFP (10 × 10)





Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.5.2 44-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR)

RENESAS

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Absolute Maximum Ratings (T_A = 25°C)

Parameter	Symbols		Conditions	Ratings	Unit
LCD voltage	VL1	VL1 voltage ^{Note 1}		–0.3 to +2.8 and –0.3 to V∟4 + 0.3	V
	VL2	VL2 voltage ^{Note 1}		-0.3 to V_{L4} + 0.3 $^{\text{Note 2}}$	V
	VL3	VL3 voltage ^{Note 1}		–0.3 to V_{L4} + 0.3 $^{\text{Note 2}}$	V
	VL4	VL4 voltage ^{Note 1}		–0.3 to +6.5	V
	VLCAP	CAPL, CAPH vol	tage ^{Note 1}	–0.3 to VL4 + 0.3 $^{\text{Note 2}}$	V
VLO	VLOUT	COM0 to COM7, SEG0 to	External resistance division method	-0.3 to V _{DD} + 0.3 ^{Note 2}	V
		SEG38,	Capacitor split method	-0.3 to V_{DD} + 0.3 $^{\text{Note 2}}$	
	output volta	output voltage	Internal voltage boosting method	-0.3 to V _{L4} + 0.3 ^{Note 2}	

Notes 1. This value only indicates the absolute maximum ratings when applying voltage to the VL1, VL2, VL3, and VL4 pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to Vss via a capacitor (0.47 μ F ± 30%) and connect a capacitor (0.47 μ F ± 30%) between the CAPL and CAPH pins.

- 2. Must be 6.5 V or lower.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Vss : Reference voltage



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Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	Voh1	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120,	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -10 \ mA \end{array} \end{array} \label{eq:eq:entropy}$	EVDD-1.5			V
		P125 to P127, P130, P140 to P147	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -3.0 \ mA \end{array}$	EVDD-0.7			V
			$\begin{array}{l} 2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}, \\ \text{I}_{\text{OH1}} = -2.0 \text{ mA} \end{array}$	EV _{DD} -0.6			V
			$\begin{array}{l} 1.8 \ V \leq EV_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -1.5 \ mA \end{array}$	EVDD-0.5			V
			1.6 V \leq EV _{DD} \leq 5.5 V, Іон1 = -1.0 mA	EVDD-0.5			V
	Vон2	P20, P21	1.6 V \leq V_DD \leq 5.5 V, IOH2 = -100 μ A	VDD-0.5			V
Output voltage, low	Vol1	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120,	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 20 \ mA \end{array} \end{array} \label{eq:eq:optimal_states}$			1.3	V
		P125 to P127, P130, P140 to P147	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 8.5 \ mA \end{array} \end{array} \label{eq:eq:entropy}$			0.7	V
			$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 3.0 \ mA \end{array} \end{array} \label{eq:eq:entropy}$			0.6	V
			$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V},$ $I_{\text{OL1}} = 1.5 \text{ mA}$			0.4	V
			$eq:local_$			0.4	V
			$1.6 \text{ V} \leq \text{EV}_{\text{DD}} < 5.5 \text{ V},$ $I_{\text{OL1}} = 0.3 \text{ mA}$			0.4	V
	Vol2	P20, P21	$1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol2 = 400 μ A			0.4	V
	Vol3	P60, P61	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL3}} = 15.0 \ mA \end{array} \end{array} \label{eq:eq:entropy}$			2.0	V
			$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL3}} = 5.0 \ mA \end{array} \end{array} \label{eq:eq:entropy}$			0.4	V
			$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V},$ Iol3 = 3.0 mA			0.4	V
			$1.8 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V},$ Iol3 = 2.0 mA			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD}} < 5.5 \text{ V},$ lol3 = 1.0 mA			0.4	V

Caution P10, P12, P15, P17 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Current flowing to VDD.
 - 2. When high speed on-chip oscillator and high-speed system clock are stopped.
 - 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
 - 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
 - 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
 - 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
 - 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
 - 8. Current flowing only during data flash rewrite.
 - 9. Current flowing only during self programming.
 - **10.** For shift time to the SNOOZE mod.
 - 11. Current flowing only to the LCD controller/driver. The supply current value of the RL78 microcontrollers is the sum of the LCD operating current (ILCD1, ILCD2 or ILCD3) to the supply current (IDD1 or IDD2) when the LCD controller/driver operates in an operation mode or HALT mode. Not including the current that flows through the LCD panel.

The TYP. value and MAX. value are following conditions.

- When fsuB is selected for system clock, LCD clock = 128 Hz (LCDC0 = 07H)
- 4-Time-Slice, 1/3 Bias Method
- **12.** Not including the current that flows through the external divider resistor when the external resistance division method is used.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fcLK: CPU/peripheral hardware clock frequency
 - 4. Temperature condition of the TYP. value is T_A = 25°C



TI/TO Timing





2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

$(1A40 \ 10 \ +05 \ C, 1.0 \ V \le EVDD - VDD \le 5.5 \ V, VSS - EVSS - 0 \ V)$									
Parameter	Symbol	Conditions	HS (hig main)	h-speed Mode	LS (low main)	/-speed Mode	LV (low main)	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		$2.4 \text{ V} \leq \text{EV}\text{DD} = \text{V}\text{DD} \leq 5.5 \text{ V}$		f мск/6		fмск/6		f мск/6	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 2$		4.0		1.3		0.6	Mbps
		$1.8 \text{ V} \le \text{EV}_{\text{DD}} = \text{V}_{\text{DD}} \le 5.5 \text{ V}$				f мск/6		fмск/6	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 2$				1.3		0.6	Mbps
		$1.6 \text{ V} \le \text{EV}_{\text{DD}} = \text{V}_{\text{DD}} \le 5.5 \text{ V}$						f мск/6	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 2$						0.6	Mbps

(1) During communication at same potential (UART mode) ($T_A = -40$ to +85°C, 1.6 V \leq EV_{DD} = V_{DD} \leq 5.5 V, V_{SS} = EV_{SS} = 0 V)

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

HS (high-speed main) mode:	24 MHz (2.7 V \leq V _{DD} \leq 5.5 V)
	16 MHz (2.4 V \leq V _{DD} \leq 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V \leq V _{DD} \leq 5.5 V)
LV (low-voltage main) mode:	4 MHz (1.6 V \leq V _{DD} \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).





CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM number (g = 1)

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage								
	Reference voltage (+) = AVREFP	Reference voltage (+) = VDD	Reference voltage (+) = VBGR							
Input channel	Reference voltage (-) = AVREFM	Reference voltage (-) = Vss	Reference voltage (-) = AVREFM							
ANIO, ANI1	-	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).							
ANI16 to ANI23	Refer to 2.6.1 (2).									
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1) .		-							

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD}} = \text{V}_{\text{DD}} \le 5.5 \text{ V}, 1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS}} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{\text{REFP}}, \text{Reference voltage (-)} = \text{AV}_{\text{REFM}} = 0 \text{ V})$

Parameter	Symbol	Condit	ions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL 10-bit resolution	$1.8~V \leq V_{\text{DD}} \leq 5.5~V$		1.2	±3.5	LSB	
		AV _{REFP} = V _{DD} ^{Note 3}	$1.6~\text{V} \leq \text{V}_\text{DD} \leq 5.5~\text{V}^{\text{Note 4}}$		1.2	±7.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.5625		39	μs
		voltage, and temperature sensor output voltage (HS	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	17		39	μs
		(high-speed main) mode)					
Zero-scale error ^{Notes 1, 2}	scale error ^{Notes 1, 2} E _{ZS}	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$1.8 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$			±0.25	%FSR
			$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±0.50	%FSR
Full-scale error Notes 1, 2	E _{FS}	s 10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$1.8~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.25	%FSR
			$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±0.50	%FSR
Integral linearity	ILE	10-bit resolution	$1.8~V \leq V_{\text{DD}} \leq 5.5~V$			±2.5	LSB
error ^{Note 1}		AV _{REFP} = V _{DD} ^{Note 3}	$1.6~V \leq V_{\text{DD}} \leq 5.5~V^{\text{Note 4}}$			±5.0	LSB
Differential linearity	DLE	10-bit resolution	$1.8~V \leq V_{\text{DD}} \leq 5.5~V$			±1.5	LSB
error ^{Note 1}		AV _{REFP} = V _{DD} ^{Note 3}	$1.6~V \leq V_{\text{DD}} \leq 5.5~V^{\text{Note 4}}$			±2.0	LSB
Analog input voltage	VAIN	Internal reference voltage			$V_{\text{BGR}}^{\text{Note 5}}$		V
		(2.4 V \leq V_{DD} \leq 5.5 V, HS (high-	2.4 V \leq V _{DD} \leq 5.5 V, HS (high-speed main) mode)				
	VBGR	Temperature sensor output vol (2.4 V \leq V _{DD} \leq 5.5 V, HS (high-		VTMPS25 Note 5	i	V	

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When AV_{REFP} < V_{DD}, the MAX. values are as follows.
 - Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

- 4. Values when the conversion time is set to 57 μ s (min.) and 95 μ s (max.).
- 5. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

LVD Detection Voltage of Interrupt & Reset Mode

(TA = -40 to +85°C, VPDR \leq EVDD = VDD \leq 5.5 V, Vss = EVss = 0 V)

Parameter	Symbol		Conc	litions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVDA0	VPOC2	, VPOC1, VPOC0 = 0, 0, 0	, falling reset voltage	1.60	1.63	1.66	V
mode	VLVDA1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	V LVDA3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDB1	VPOC2	, VPOC1, VPOC0 = 0, 0, 1	, falling reset voltage	1.80	1.84	1.87	V
	VLVDB2	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V	
				Falling interrupt voltage	1.90	1.94	1.98	V
	VLVDB3		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
			Falling interrupt voltage	2.00	2.04	2.08	V	
	VLVDB4	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V	
			Falling interrupt voltage	3.00	3.06	3.12	V	
	VLVDC0	VPOC2,	, VPOC1, VPOC0 = 0, 1, 0	, falling reset voltage	2.40	2.45	2.50	V
	VLVDC1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
			Falling interrupt voltage	2.50	2.55	2.60	V	
	VLVDC2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	VPOC2	, VPOC1, VPOC0 = 0, 1, 1	, falling reset voltage	2.70	2.75	2.81	V
	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

2.6.5 Supply voltage rise time

(T_A = -40 to +85°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 30.4 AC Characteristics.

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Absolute Maximum Ratings (T_A = 25°C)

		-				
Parameter	Symbols		Conditions	Ratings	Unit	
LCD voltage	V _{L1}	V _{L1} voltage ^{Note 1}		-0.3 to +2.8 and -0.3 to V _{L4} + 0.3	V	
	VL2	VL2 voltage ^{Note 1}		-0.3 to $V_{\rm L4}$ + 0.3 $^{\rm Note\ 2}$	V	
	VL3	VL3 voltage ^{Note 1}	VL3 voltage ^{Note 1} -0.3 to VL4 + 0.1			
	VL4	VL4 voltage ^{Note 1}		-0.3 to +6.5	V	
	VLCAP	CAPL, CAPH vol	tage ^{Note 1}	–0.3 to V_{L4} + 0.3 $^{\text{Note 2}}$	V	
	Vlout	COM0 to COM7, SEG0 to	External resistance division method	-0.3 to V _{DD} + 0.3 ^{Note 2}	V	
		SEG38,	Capacitor split method	-0.3 to V _{DD} + 0.3 ^{Note 2}		
	output voltage		Internal voltage boosting method	-0.3 to V _{L4} + 0.3 ^{Note 2}		

Notes 1. This value only indicates the absolute maximum ratings when applying voltage to the VL1, VL2, VL3, and VL4 pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to Vss via a capacitor (0.47 μ F ± 30%) and connect a capacitor (0.47 μ F ± 30%) between the CAPL and CAPH pins.

- 2. Must be 6.5 V or lower.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Vss : Reference voltage



Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Input voltage, high	VIH1	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	Normal input buffer	0.8EVDD		EVDD	V
	VIH2	P10, P11, P15, P16	TTL input buffer 4.0 V \leq EV _{DD} \leq 5.5 V	2.2		EVDD	V
			TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}$	2.0		EVDD	V
			TTL input buffer 2.4 V \leq EV _{DD} $<$ 3.3 V	1.50		EVDD	V
	VIH3	P20, P21	0.7Vdd		Vdd	V	
	VIH4	P60, P61	0.7EVDD		EVDD	V	
	VIH5	P121 to P124, P137, EXCLK, EXCLKS	, RESET	0.8VDD		Vdd	V
Input voltage, low	VIL1	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	Normal input buffer	0		0.2EV _{DD}	V
	V _{IL2} P10, P11, P15, P16	TTL input buffer 4.0 V \leq EV _{DD} \leq 5.5 V	0		0.8	V	
			TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer 2.4 V \leq EV _{DD} $<$ 3.3 V	0		0.32	V
	VIL3	P20, P21		0		0.3V _{DD}	V
	VIL4	P60, P61		0		0.3EVDD	V
	VIL5	P121 to P124, P137, EXCLK, EXCLKS	, RESET	0		0.2VDD	V

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD}} = \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS}} = 0 \text{ V})$



Caution The maximum value of Vi of pins P10, P12, P15, and P17 is EVDD, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.





UART mode bit width (during communication at different potential) (reference)



 $Cb[F]: \ Communication \ line \ (TxDq) \ load \ capacitance, \ Vb[V]: \ Communication \ line \ voltage$

- **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 1)
- fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))





CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM number (g = 1)

(2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI16 to ANI23

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD} = \text{V}_{DD} \le 5.5 \text{ V}, 2.4 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = EV _{DD} = V _{DD} ^{Note 3}	$2.4~V \leq AV_{\text{REFP}} \leq 5.5~V$		1.2	±5.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.125		39	μs
		$AV_{REFP} = EV_{DD} = V_{DD}^{Note 3}$	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.1875		39	μs
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = EV _{DD} = V _{DD} ^{Note 3}	$2.4~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.35	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution AV _{REFP} = EV _{DD} = V _{DD} ^{Note 3}	$2.4~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = EV _{DD} = V _{DD} ^{Note 3}	$2.4~V \leq AV_{\text{REFP}} \leq 5.5~V$			±3.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = EV _{DD} = V _{DD} ^{Note 3}	$2.4 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$			±2.0	LSB
Analog input voltage	VAIN	ANI16 to ANI23		0		AVREFP and EVDD	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < EV_{DD} = V_{DD}$, the MAX. values are as follows.

Overall error: Add \pm 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.



3.11 Timing Specifications for Switching Flash Memory Programming Modes (T_A = -40 to +105°C, 2.4 V \leq EV_{DD} = V_{DD} \leq 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.
- **Remark** tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.
 - $t_{\text{su:}}$ Time to release the external reset after the TOOL0 pin is set to the low level
 - the: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)



4.2 44-pin Products

R5F10RF8AFP, R5F10RFAAFP, R5F10RFCAFP R5F10RF8GFP, R5F10RFAGFP, R5F10RFCGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36



NOTE

Each lead centerline is located within 0.20 mm of its true position at maximum material condition.

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у

ZD

ZE

0.10

1.00

1.00



4.3 48-pin Products

R5F10RG8AFB, R5F10RGAAFB, R5F10RGCAFB R5F10RG8GFB, R5F10RGAGFB, R5F10RGCGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP48-7x7-0.50	PLQP0048KF-A	P48GA-50-8EU-1	0.16



NOTE

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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ΖE

0.75



R5F10RLAANB, R5F10RLCANB R5F10RLAGNB, R5F10RLCGNB

<r></r>	JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]	
	P-HWQFN64-8x8-0.40	PWQN0064LA-A	P64K8-40-9B5-4	0.16	

Unit: mm









Reference	Dimensions in millimeters				
Symbol	Min	Nom	Max		
D	7.95	8.00	8.05		
E	7.95	8.00	8.05		
A	_	_	0.80		
A ₁	0.00		_		
b	0.17	0.20	0.23		
е	_	0.40	—		
Lp	0.30	0.40	0.50		
х	—	_	0.05		
у	_		0.05		
ZD	_	1.00	—		
ZE	_	1.00	—		
C2	0.15	0.20	0.25		
D ₂	_	6.50	_		
E ₂	—	6.50	_		

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